Shenzhen RICKY Electronic Technology Co.,Ltd

RS25 Series 25A TRIACs

DESCRIPTION:

High current density due to double mesa technology, SIPOS and Glass Passivation.

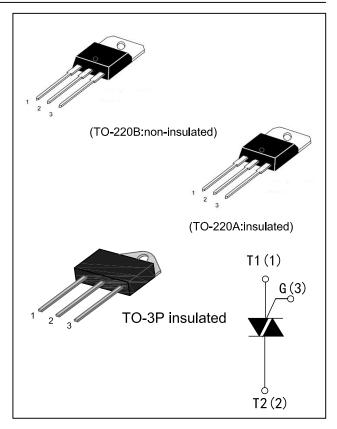
RS25A/RS25B/RS25Z series triacs is suitable for general purpose AC switching, They can be used as an ON/OFF function in applications such as static relays, heating regulation, induction motor stating circuits... or for phase contol operation, light dimmers, motor speed controllers.

RS25-CW-BW Series are 3 quadrants triacs, They are specially recommended for use on inductive loads.

RS25A RS25Z series provide a 2500V RMS isolation voltage from all three terminals to external heat sink.

MAIN FEATURES

Symbol	Value	Unit
IT(RMS)	25	Α
VDRM/VRRM	600 / 800	V
Vтм	1.55	V



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit	
Storage junction temperature range	Tstg	-40 to +150	°C	
Operrating junction temperature range		Tj	-40 to +125	°C
	RS25x06		600	V
Repetitive Peak Off-state Voltage (Tj=25°C)	RS25x08	VDRM	800	
Repetitive Peak Reverse Voltage (Tj=25°C)		VRRM		
		1		
Non repetitive Surge Peak Off-state Voltage (tp=10ms,Tj=25 °C)	VDSM	V _{DRM} +100	
Non repetitive Peak Reverse Voltage (tp=10m	VRSM	V _{RRM} +100	v	
RMS on-state current (full sine wave)	TO-220A Tc=75°C	IT(RMS)	25	A
Trivis on-state current (run sine wave)	TO-220B Tc=100°C	TI(KWS)		
Non repetitive surge peak on-state current	f=60Hz,t=16.7ms	ITOM	260	Α
(full cycle,Tj=25°C)	f=50Hz,t=20ms	- ITSM	250	
I²t Value for fusing	tp=10ms	l²t	340	A²s
Critical rate of rise of on-state current (IG=2×IG⊤,tr≤100ns,f=120Hz,Tj=125°C)	dl /dt	50	A/µs	
Peak gate current (tp=20us,Tj=125°C)			4	Α
Peak Gate Power Dissipation (tp=20us,Tj=125 °C)			10	W
Average gate power dissipation (Tj=125 °C)			1	W

TEL:+86-0755-89519740



ELECTRICAL CHARACTERISTICS (Tj=25°C unless otherwise specified)

Symbol	Took Condition	Ouadrant		Limits		11	
Symbol	Test Condition	Quadrant		CW(C)	BW(B)	Unit	
Igт	\/p=42\/ Di =22O	1-11-111	MAX.	35	50	mA	
VGT	VD=12V RL=33Ω		MAX.	1.3		V	
VGD	VD=VDRM RL=3.3KΩ Tj =125℃	1-11-111	MIN.	0.2		V	
lı.	 IG=1.2IGT	I-III	MAX.	70	80	mA	
IL	1.2161	II	MAX.	80	100	mA	
lн	IT =100mA			50	75	mA	
dV/dt	VD=67%VDRM gate open Tj=125℃		MIN.	500	1000	V/µs	
(dl/dt)c	Without snubber Tj=125℃		MIN.	13	22	A/ms	

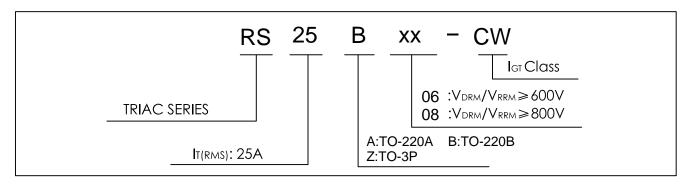
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
VTM	Iτм=35A,tp=380μs Tj=25℃		1.55	V
IDRM VD=VDF	VD=VDRM VR=VRRM	Tj=25℃	5	μΑ
	VU-VUKW VK-VKKW	Tj=125℃	3	mA

THERMAL RESISTANCES

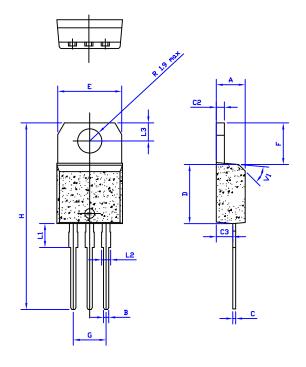
Symbol	Param	Value	Unit		
Rth(j-c)	Junction to Case(AC)		1.7	°C/W	
	Junction to Case(AC)	TO-220B	0.8	C/VV	
Rth(j-a)	Junction to ambient	TO-220A	60	°C/W	
	(S=1cm ²)	TO-220B	60	C/VV	

ORDERING INFORMATION

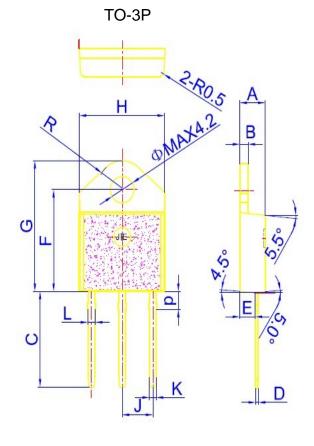


PACKAGE MECHANICAL DATA

TO-220A insulated package and TO-220B non-insulated package



	Dimensions						
Ref.	Millimeters			Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
Α	4.4		4.6	0.173		1.181	
В	0.61		0.88	0.024		0.034	
С	0.46		0.70	0.018		0.027	
C2	1.23		1.32	0.048		0.051	
C3	2.4		2.72	0.094		0.107	
D	8.6		9.7	0.338		0.382	
Е	9.8		10.4	0.386		0.409	
F	6.2		6.6	0.244		0.259	
G	4.8		5.4	0.189		0.213	
Н	28.0		29.8	11.0		11.7	
L1		3.75			0.147		
L2	1.14		1.7	0.044		0.066	
L3	2.65		2.95	0.104		0.116	
V1		40°			40°		



	Dimensions						
Ref.	Millimeters			Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
Α	4.4		4.6	0.173	433.73.40	0.181	
В	1.45		1.55	0.057		0.061	
С	14.35		15.6	0.565		0.614	
D	0.5		0.7	0.020		0.028	
Е	2.7		2.9	0.106		0.114	
F	15.8		16.5	0.622		0.650	
G	20.4		21.1	0.815		0.831	
Н	15.1		15.5	0.594		0.610	
J	5.4		5.65	0.213		0.222	
K	1.2		1.4	0.047		0.055	
L	1.35		1.50	0.053		0.059	
Р	2.8		3.0	0.110		0.118	
R		4.6			0.181		

RICKY

FIG.1:Maximum power dissipation versus RMS on-state current(full cycle)

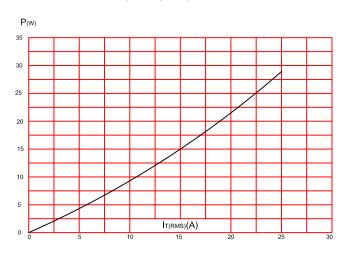


FIG.2:RMS on-state current versus case temperature(full cycle)

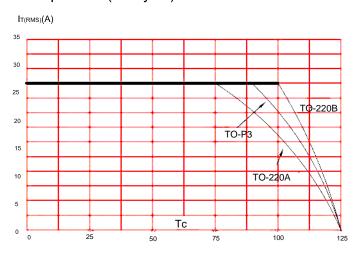


FIG.3:On-state characteristics (maximum values).

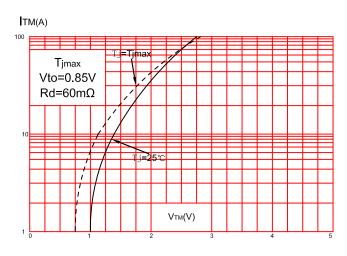


FIG.4:Surge peak on-state current versus number of cycles.

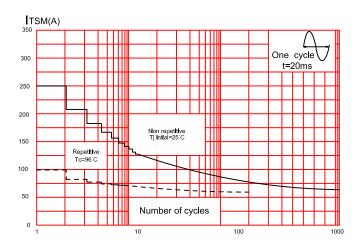


FIG.5:Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<10ms,and corresponding value of l²t.

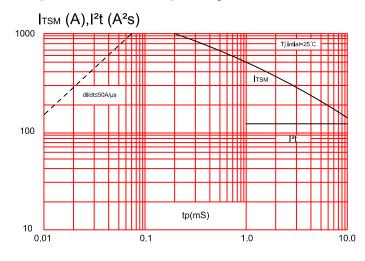


FIG.6:Relative variations of gate trigger current, holding current and latching current versus junction temperature(typical values)

